

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

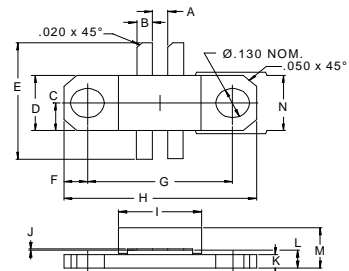
The ASI CBSL30B is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CB0}	48 V
V_{CES}	45 V
V_{EBO}	4.0 V
P_{DISS}	43 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	3.0 °C/W

PACKAGE STYLE .250 BAL FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.060 / 1.52
B	.055 / 1.40	.065 / 1.65
C		.125 / 3.18
D	.243 / 6.17	.255 / 6.48
E	.630 / 16.00	.670 / 17.01
F		.092 / 2.34
G	.555 / 14.10	.565 / 14.35
H	.739 / 18.77	.750 / 19.05
I	.315 / 8.00	.327 / 8.31
J	.002 / 0.05	.006 / 0.15
K	.055 / 1.40	.065 / 1.65
L	.075 / 1.91	.095 / 2.41
M		.190 / 4.83
N	.245 / 6.22	.257 / 6.53

ORDER CODE: ASI10583
CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 50 mA	48	50	---	V
BV_{CEO}	I _C = 20 mA	25	30	---	V
BV_{EBO}	I _E = 5 mA	3.5	4.0	---	V
I_{CB0}	V _{CB} = 24 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	20		100	---
C_{OB}	V _{CB} = 24 V f = 1.0 MHz			25	pF
P_G	V _{CC} = 24 V I _{CQ} = 2 X 75 mA f = 960 MHz P _{OUT} = 30 W	7.5			dB